

Supplementary Information: Electron pumping in graphene mechanical resonators

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We consider a suspended graphene resonator as described in [1, 2]. The dynamical equation for the out-of-plane deformation from equilibrium $a(t)$ is given by (see the respective Appendixes on the form of the forces),

$$\rho \frac{\partial^2 a}{\partial t^2} = \mathcal{F}_S + \mathcal{F}_D + \mathcal{F}_E \quad (1)$$

where \mathcal{F}_S , \mathcal{F}_D , \mathcal{F}_E are the time dependent restoring elastic, damping and electrostatic forces (or pressures) respectively, in units of m^{-2} . ρ is the mass density. The total restoring elastic force, ignoring second order terms due to bending forces κ and $O(h^2)$, reduces to,

$$\mathcal{F}_S = -\frac{64}{3} \frac{\lambda + 2\mu}{L^4} (a^3 + 3a^2 h_0 + 3ah_0^2) + \frac{8\Delta L}{L^3} (\lambda + 2\mu)a \quad (2)$$

obtained by minimizing elastic energy. Damping is treated phenomenologically via,

$$\mathcal{F}_D = -\frac{\rho}{\tau_d} \frac{\partial a}{\partial t} \quad (3)$$

τ_d can be easily obtained from quality factor Q measured in experiments. Q is defined to be $Q = \omega_0/\Delta\omega = \omega_0\tau_d/2$, where $\Delta\omega$ is the so called bandwidth of the resonance peak. Reported Q is around 100 [1, 2] at room temperature, depending on many factors. For example, temperature dependence of $Q \propto T^{-0.36}$ was found, for $T < 100K$ [2]. And a record $Q \approx 100,000$ at $90mK$ was reported [3]. Mass density of graphene assumed to be $\rho \approx 7.4 \times 10^{-6} kgm^{-2}$. Lastly, the electrostatic force is modelled as,

$$\mathcal{F}_E = \frac{C_T^2 V_{dc} V_{ac}}{\epsilon_0} \cos(\omega t) \quad (4)$$

neglecting $O(V_{ac}^2)$ and other non-linear terms. $C_T = [\epsilon_0^{-1}(d + h_0) + \epsilon_{SiO_2}^{-1} t_{SiO_2}]^{-1}$ is the total effective capacitance due to the back-gate oxide and air dielectric, d being the perpendicular distance of the unstrained graphene from the substrate.

We are interested in the steady state solution to the dynamical equation i.e. $a(\omega) = |a|\exp(i\phi)$. We seek an approximate solution through an iterative technique used in the Duffing model [4, 5]. For convenience, we rewrite the dynamical equation as,

$$\rho \ddot{a} = -k_0 a - k_1 a^2 - k_2 a^3 - \frac{\rho}{\tau_d} \dot{a} + f \cos(\omega t) \quad (5)$$

where

$$k_0 = \frac{64(\lambda + 2\mu)h_0^2}{L^4} - \frac{8\Delta L}{L^3}(\lambda + 2\mu), \quad k_1 = \frac{64(\lambda + 2\mu)h_0}{L^4}, \quad k_2 = \frac{64(\lambda + 2\mu)}{3L^4}, \quad f = \frac{C_T^2 V_{dc} V_{ac}}{\epsilon_0} \quad (6)$$

In the spring constant term k_0 , we consider only the case for $\Delta L \leq 0$. k_2 contributes to the Duffing force, and renders the spring more stiff (soft) if positive (negative). In the former, the effect will be a shift of resonance with increasing driving force. And at larger driving force would lead to bistability and hysteresis [2].

The frequency response $a(\omega)$ around the resonant frequency $\omega_0 \equiv \sqrt{k_0/\rho}$ has the following approximate solution,

$$\left[(\omega_0^2 - \omega^2)|a| + \frac{3k_2}{4\rho}|a|^3 \right]^2 + \left(\frac{\omega|a|}{\tau_d} \right)^2 = \left(\frac{f}{\rho} \right)^2 \quad (7)$$

$$\tan\phi = \frac{\omega|a|}{\tau_d \left[(\omega_0^2 - \omega^2)|a| + \frac{3k_2}{4\rho}|a|^3 \right]} \quad (8)$$

Note that a^2 terms affects the higher harmonics $2\omega_0$. These converge to the Lorentz model solutions if we set $k_2 = 0$. In the linear regime, i.e. $k_2 = 0$, the response at $\omega = \omega_0$ goes as $|a| = 2Qf/\rho\omega_0^2$. When $k_2 \neq 0$, $|a|$ follows,

$$\frac{9k_2^2}{16}|a|^6 + \frac{k_0^2}{4Q^2}|a|^2 = f^2 \quad (9)$$

From this, we can define a threshold driving force f_{th} where $|a(\omega = \omega_0)|$ starts to deviate from linearity i.e. $|a| \propto f$,

$$f_{th} \approx \sqrt{\frac{k_0^3}{36Q^3k_2}} \quad (10)$$

As evident, ρ has no effect on f_{th} , and a larger Q yields a smaller f_{th} i.e. increased sensitivity to non-linearity. However, a larger Q is desirable to achieve a larger resonance $|a(\omega = \omega_0)|$.

APPENDIX A: ELECTROSTATIC FORCES

The electrostatic force is modelled as,

$$\mathcal{F}_E^{tot} = \frac{1}{2} \frac{C_T^2}{\epsilon_0} V_{bg}^2 \approx \frac{1}{2} \frac{C_T^2}{\epsilon_0} (V_{dc}^2 + 2V_{dc}V_{ac}\cos(\omega t)) \equiv \mathcal{F}_E^{eq} + \mathcal{F}_E \quad (A1)$$

neglecting $O(V_{ac}^2)$. $C_T = [\epsilon_0^{-1}(d + h_0) + \epsilon_{SiO_2}^{-1}t_{SiO_2}]^{-1}$ is the total effective capacitance (per unit area) due to the back-gate oxide and air dielectric. d is the perpendicular distance of graphene from the substrate when unstrained.

APPENDIX B: ELASTIC FORCES

The position of a 2D membrane can be described by the in-plane and out-of-plane deformation field given by $\mathbf{u}(x, y) = [u_x(x, y), u_y(x, y)]$ and $h(x, y)$. In the linear approximation, the strain tensor is given by,

$$u_{\alpha\beta} = \frac{1}{2}(\partial_\alpha u_\beta + \partial_\beta u_\alpha + \partial_\alpha \partial_\beta h) \quad (B1)$$

The elastic free energy is given by [6, 7],

$$\begin{aligned} \mathcal{E} &= \int dx dy \left[\frac{1}{2} \kappa (\nabla^2 h)^2 + \frac{1}{2} \lambda (u_{xx} + u_{yy})^2 + \mu (u_{xx}^2 + u_{yy}^2 + 2u_{xy}^2) - \mathcal{F}_E^{eq} h \right] \\ &\approx \int dx \left[\frac{1}{2} \kappa (\nabla^2 h)^2 + \frac{1}{2} (\lambda + 2\mu) u_{xx}^2 - \mathcal{F}_E^{eq} h \right] \end{aligned} \quad (B2)$$

where $\kappa \approx 1eV$ is the bending rigidity, $\mu \approx 9eV\text{\AA}^{-2}$ and $\lambda \approx 2eV\text{\AA}^{-2}$ are the Lamé constants of graphene. Experiments [8] measures an elastic constant for graphite $c_{11} = 106 \times 10^{10} Nm^{-2} \approx 1TPa$. For graphene, we have the relation $c_{11}d_{in} = \lambda + 2\mu$. Using an interlayer separation distance of $d_{in} = 0.335nm$ [9], we $c_{11}d_{in} \approx 355Nm^{-1}$. This is in good agreement with the values of Lamé constants we assumed. Recent measurement [10] of the Young's modulus of graphene yields $E_{2d} = 342Nm^{-1}$. Note that by definition, $E_{2d} = c_{11}d_{in}$.

\mathcal{F}_E^{eq} is the pressure induced by the bottom electrostatic gate. Assuming homogeneity along transverse direction, we arrive to a one-dimensional problem. Minimizing \mathcal{E} in Eq. B2 yields us the following Euler-Lagrange equations,

$$\begin{aligned} \kappa \partial_x^4 h - (\lambda + 2\mu) \left[\frac{3}{2} (\partial_x h)^2 \partial_x^2 h + \partial_x u_x \partial_x^2 h + \partial_x h \partial_x^2 u_x \right] &= \mathcal{F}_E^{eq} \\ \partial_x^2 u_x + \partial_x h \partial_x^2 h &= 0 \end{aligned} \quad (B3)$$

where the latter implies the longitudinal strain is constant i.e.

$$u_{xx} = \text{constant} \quad (\text{B4})$$

Finally, the differential equation governing $h(x)$ is,

$$\kappa \partial_x^4 h - (\lambda + 2\mu) u_{xx} \partial_x^2 h = \mathcal{F}_E^{eq} \quad (\text{B5})$$

The differential equation for h then reduces to,

$$-(\lambda + 2\mu) u_{xx} \partial_x^2 h = \mathcal{F}_E^{eq} \quad (\text{B6})$$

whose explicit solution with the boundary condition $h(\pm L/2) = 0$ is,

$$h(x) \approx \frac{\mathcal{F}_E^{eq}(L^2 - 4x^2)}{8(\lambda + 2\mu)u_{xx}} \equiv h_0 - \frac{4h_0}{L^2}x^2 \quad \text{where} \quad h_0 = \frac{\mathcal{F}_E^{eq}L^2}{8(\lambda + 2\mu)u_{xx}} \quad (\text{B7})$$

where h_0 is the maximum deflection i.e. at $x = 0$. Including the second order terms, the expression can be rather complicated [11]. With the profile $h(x)$, simple geometry allows us to relate u_{xx} with h_0 as per Eq. C9. Then the elastic force equation reduces from Eq. B6 to,

$$\mathcal{F}_S^{eq} = -\frac{64}{3}(\lambda + 2\mu)\frac{h_0^3}{L^4} + \frac{8\Delta L}{L^3}(\lambda + 2\mu)h_0 = \mathcal{F}_E^{eq} \quad (\text{B8})$$

where we included the possibility of an initial tension, $\Delta L < 0$. Elastic forces due to deformation a away from the equilibrium can then be described by,

$$\mathcal{F}_S = -\frac{64}{3}\frac{\lambda + 2\mu}{L^4}(a^3 + 3a^2h_0 + 3ah_0^2) + \frac{8\Delta L}{L^3}(\lambda + 2\mu)a \quad (\text{B9})$$

APPENDIX C: DEFORMATION AND GATING

Next we shall determine u_{xx} . Following [12], it is defined as,

$$u_{xx} = \frac{L' - (L + \Delta L)}{L + \Delta L} \approx \frac{L' - L}{L} - \frac{\Delta L}{L} \quad (\text{C1})$$

where L' is the length of the strained graphene,

$$L' = 2 \int_0^{L/2} dx \sqrt{1 + |\nabla h|^2} \approx L + \int_0^{L/2} dx (\partial_x h)^2 = \frac{L^3(\mathcal{F}_E^{eq})^2}{24(\lambda + 2\mu)^2 u_{xx}^2} + L \quad (\text{C2})$$

L is trench length and $L + \Delta L$ is length in absense of strain. Hence, solving u_{xx} then reduces to finding the root of,

$$u_{xx}^3 + \frac{\Delta L}{L}u_{xx}^2 - \frac{L^2(\mathcal{F}_E^{eq})^2}{24(\lambda + 2\mu)^2} = 0 \quad (\text{C3})$$

No initial tension or slack: If $\Delta L = 0$, we will obtain,

$$u_{xx} = \left[\frac{L^2(\mathcal{F}_E^{eq})^2}{24(\lambda + 2\mu)^2} \right]^{1/3} = \frac{8h^2}{3L^2} \quad (\text{C4})$$

Electrostatically, one can approximate \mathcal{F}_E^{eq} as,

$$\mathcal{F}_E^{eq} \approx \frac{e^2 n^2}{2\epsilon_{eff}} \quad (\text{C5})$$

where n is the carrier density in graphene and ϵ_{eff} is the effective dielectric due to air gap and back gate oxide. We ignore the curvature of graphene. Assuming that $\Delta L = 0$, we get an expression for maximum deflection h_0 at equilibrium,

$$h_0 = \left[\frac{3L^4 e^2 n^2}{128 \epsilon_{eff} (\lambda + \mu)} \right]^{\frac{1}{3}} \quad (C6)$$

With initial tension or slack: For general case of $\Delta L \neq 0$, To obtain h_0 rigorously requires solving the following the electrostatic and elasticity equations self-consistently.

$$F_E^{eq} = \frac{1}{2\epsilon_0} \left[\left(\frac{C_a}{\epsilon_0} \right)^{-1} + \left(\frac{C_{ox}}{t_{ox}} \right)^{-1} \right]^{-2} V_{dc}^2 \quad (C7)$$

$$-\frac{64}{3L^3} h_0^3 + \frac{8\Delta L}{L^2} h_0 + \frac{F_E^{eq} L}{\lambda + 2\mu} = 0 \quad (C8)$$

When $F_E^{eq} = 0$, the latter requires $h_0 = 0$ for $\Delta L \leq 0$ (tension), which is expected. Another remark. A series capacitance C_{ox} to C_a is essential as it provides stability to the electrically actuated mechanical system. A relation between u_{xx} and h_0 can be obtained from Eq. B7 and C3, yielding,

$$u_{xx}^3 + \left(\frac{\Delta L}{L} - \frac{8h_0^2}{3L^2} \right) u_{xx}^2 = 0$$

$$\Rightarrow u_{xx} = 0 \text{ or } u_{xx} = \frac{8h_0^2}{3L^2} - \frac{\Delta L}{L} \quad (C9)$$

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